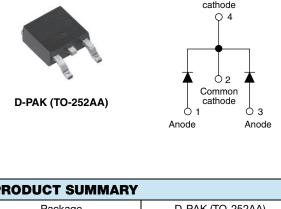
Vishay Semiconductors

Ultrafast Rectifier, 2 x 3 A FRED Pt®



Base common

PRODUCT SUMMARY					
Package	D-PAK (TO-252AA)				
I _{F(AV)}	2 x 3 A				
V _R	200 V				
V _F at I _F	1.0 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

DESCRIPTION/APPLICATIONS

Vishay Semiconductors' 200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage	V _{RRM}		200	V		
Average rectified forward current per device	I _{F(AV)}	Total device, rated V _R , T _C = 159 °C	6			
Non-repetitive peak surge current	I _{FSM}		50	А		
Peak repetitive forward current per diode	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 159 $^\circ\text{C}$	6			
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C		

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
		I _F = 3 A	-	-	1		
Forward voltage		I _F = 3 A, T _J = 125 °C	-	-	0.9	V	
	V _F	I _F = 6 A	-	-	1.2		
		I _F = 6 A, T _J = 125 °C	-	-	1.08		
Reverse leakage current I _R		$V_{R} = V_{R}$ rated	-	-	5		
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	100	μA	
Junction capacitance	C _T	V _R = 200 V	-	12	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

Document Number: 94550 Revision: 13-Jan-11 For technical questions within your region, please contact one of the following: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>







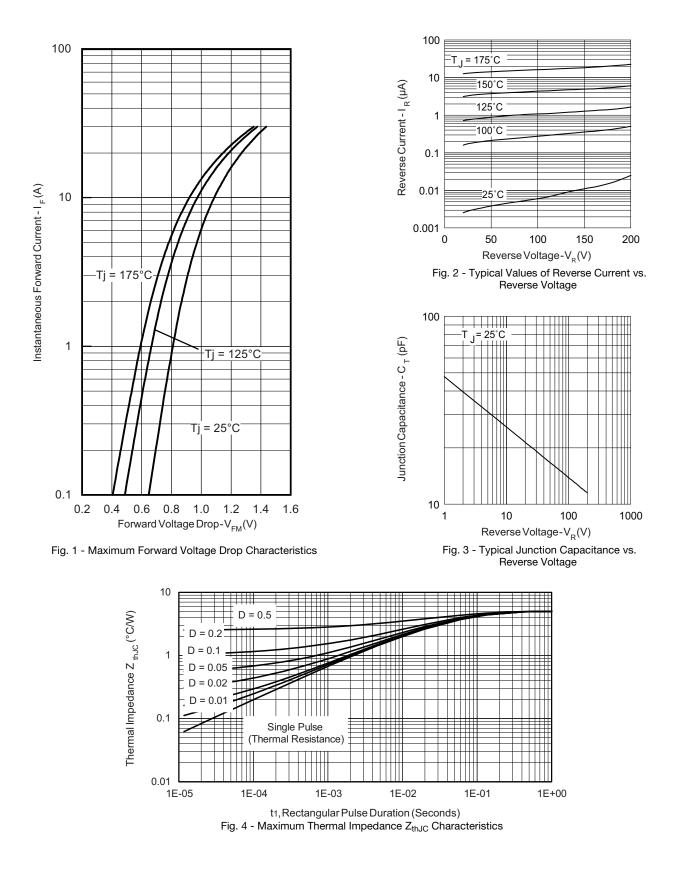
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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/1000 $	⁄μs, V _R = 30 V	-	-	35	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	19	-	ns A
		T _J = 125 °C		-	26	-	
		T _J = 25 °C	$I_F = 3 A$	-	3.1	-	
Peak recovery current	Peak recovery current	T _J = 125 °C	V _R = 160 V dI _F /dt = 200 A/µs	-	4.6	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	30	-	nC
	T _J = 125 °C]	-	60	-	nc	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}	- 65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}	-	-	5			
Thermal resistance, junction to ambient per leg	R _{thJA}	-	-	80	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	-	-	-			
Maisht		-	0.3	-	g		
Weight		-	0.01	-	oz.		
Mounting torque		6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style D-PAK 6CWH02FN			102FN		



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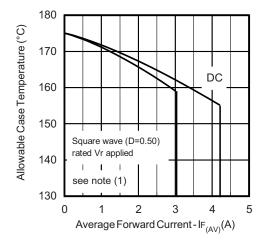


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

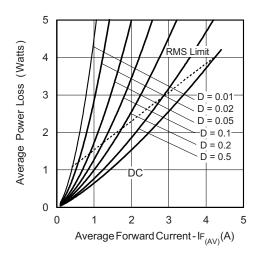


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; $I_R at V_{R1} = Rated V_R$

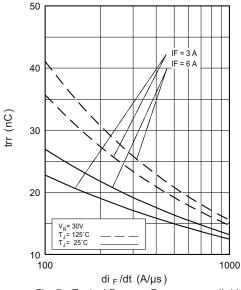


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

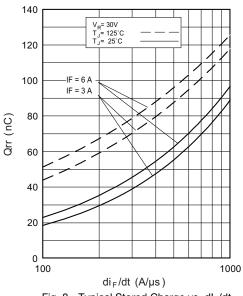


Fig. 8 - Typical Stored Charge vs. dI_F/dt



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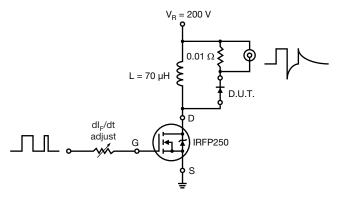


Fig. 9 - Reverse Recovery Parameter Test Circuit

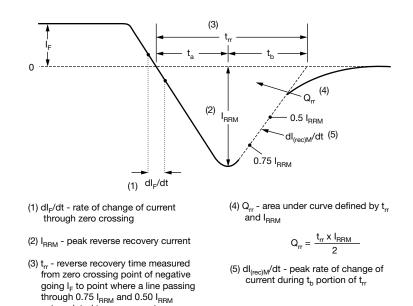


Fig. 10 - Reverse Recovery Waveform and Definitions

extrapolated to zero current.

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ORDERING INFORMATION TABLE

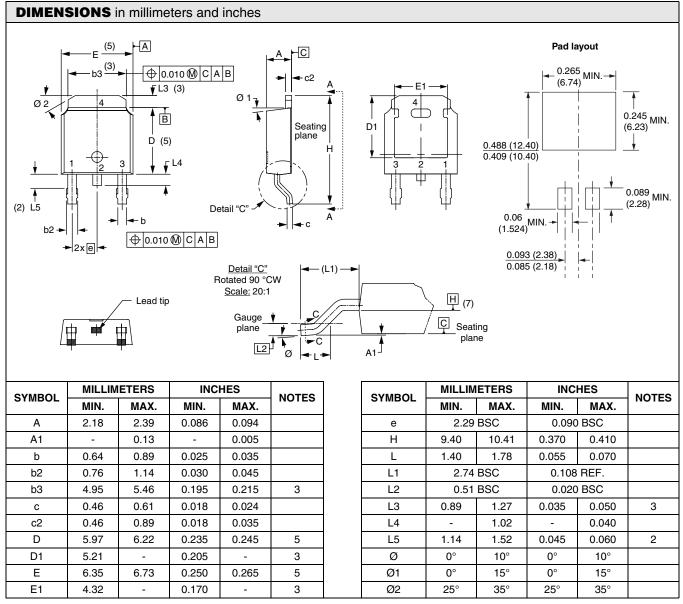
Device code	vs-	6	С	w	н	02	FN	TRL	PbF
		2	3	4	5	6	7	8	9
[1	- 1	Vish	nay Sem	niconduc	tors pro	oduct			
2	2 -	Cur	rent rati	ng (6 = 6	6 A)				
3	3 -	Cen	iter tap o	configura	ation				
4	- 1	Pac	kage ide	entifier:					
		VV =	W = D-PAK						
5	5 -	H =	H = Hyperfast recovery						
6	5 -	Volt	Voltage rating (02 = 200 V)						
7		FN	FN = TO-252AA						
8	- 1	• No	• None = Tube (50 pieces)						
		• TF	• TR = Tape and reel						
		• TF	• TRL = Tape and reel (left oriented)						
		• TF	 TRR = Tape and reel (right oriented) 						
9) -	PbF	PbF = Lead (Pb)-free						

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95016					
Part marking information www.vishay.com/doc?95059					
Packaging information <u>www.vishay.com/doc?95033</u>					



Vishay High Power Products

D-PAK (TO-252AA)



Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension uncontrolled in L5
- ⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁶⁾ Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA



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